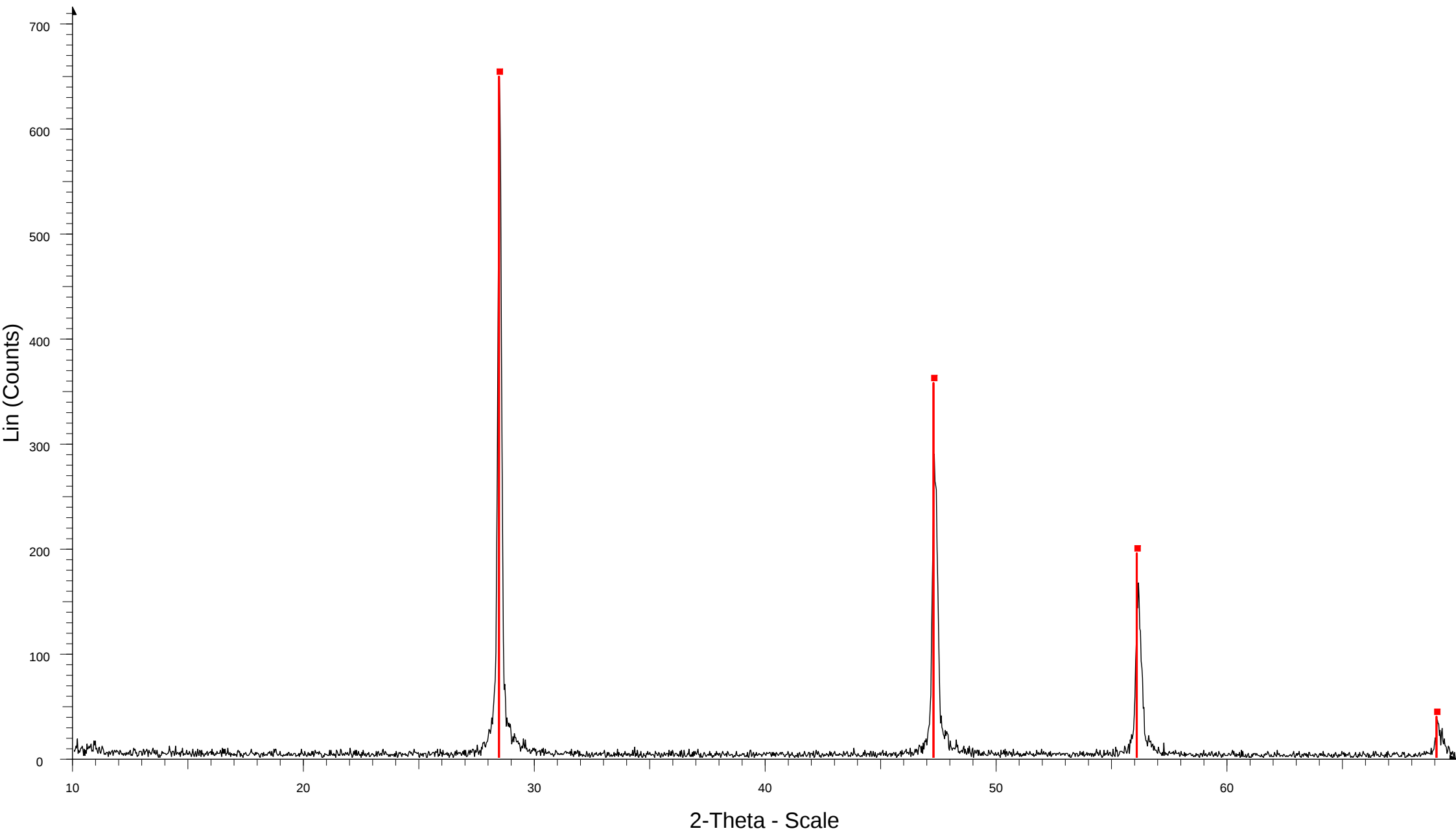


PATRÓN DE SI NIST SRM 640C 11-07-11



 PATRON SI 11-7-11 - File: PATRON SI 11-7-11.raw - Type: 2Th/Th locked - Start: 10.000 ° - End: 69.977 ° - Step: 0.030 ° - Step time: 401. s - Temp.: 23 °C - Time Started: 13 s - 2-Theta: 10.000 ° - Theta: 5.000 ° - Chi: 0.00 ° - Phi: 0.00 ° - Operations: Import

 00-027-1402 (*) - Silicon, syn - Si - Y: 100.00 % - d x by: 1. - WL: 1.5406 - Cubic - a 5.43088 - b 5.43088 - c 5.43088 - alpha 90.000 - beta 90.000 - gamma 90.000 - Face-centered - Fd-3m (227) - 8 - 160.181 - I/Ic PDF 4.7 - S-Q 10

INFORME DE CALIBRACIÓN

Si NIST 640c D8C 11-07-11

Range Number : 1

R-Values

Rexp : 29.26 Rwp : 36.22 Rp : 25.38 GOF : 1.24
Rexp` : 35.58 Rwp` : 44.03 Rp` : 33.50 DW : 1.49

Instrument

Primary radius (mm) 200.5
Secondary radius (mm) 200.5
Linear PSD 2Th angular range (°) 3
FDS angle (°) 0.6
Beam spill, sample length (mm) 14
Intensity not corrected
Full Axial Convolution
Filament length (mm) 12
Sample length (mm) 15
Receiving Slit length (mm) 12
Primary Sollers (°) 2.5
Secondary Sollers (°) 4

hkl Phase - 1 Leball method

Phase name Silicio
R-Bragg 2.906
Spacegroup 227
Cell Mass 0.000
Cell Volume (Å³) 160.05(10)
Wt% - Rietveld 0.000
Strain
Strain L 0.341(16)
Strain G 0.00(22)
e0 0.0851(63)

Lattice parameters
a (Å)

5.4294(11) **NIST 640c Certificate**
5.43311946(92)

h	k	l	m	d	Th2	I
1	1	1	8	3.13467	28.45052	213
0	2	2	12	1.91959	47.31685	126
3	1	1	24	1.63703	56.13953	70.3
2	2	2	8	1.56734	58.87444	0.634
0	0	4	6	1.35735	69.15218	15.9